General Description

SFGMOS® low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The low V_{th} series is specially designed to use in synchronous rectification power systems with low driving voltage.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switched mode power supply

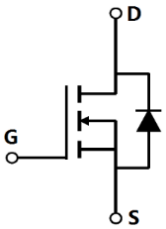
Key Performance Parameters

Parameter	Value	Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	100	V
$I_{D,\ pulse}$	64	A
$R_{DS(ON)\ max}$ @ V_{GS}=10V	8	
Q_g	60.7	nC

Marking Information

Product Name	Package	Marking
SFG10R08BF	SOP8	SFG10R08B

Package & Pin information



Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	100	V
Gate source voltage	V_{GS}	±20	V
Continuous drain current[1], T_C=25 °C	I_D	16	A
Pulsed drain current[2], T_C=25 °C	$I_{D, pulse}$	64	A
Continuous diode forward current[1], T_C=25 °C	I_S	16	A
Diode pulsed current[2], T_C=25 °C	$I_{S, Pulse}$	64	A
Power dissipation[3], T_C=25 °C	P_D	4	W
Single pulsed avalanche energy[5]	E_{AS}	130	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-ambient[4]	R	31	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	100			V	V_{GS}=0 V, I_D=250 A
Gate threshold voltage	$V_{GS(th)}$	1.0		2.5	V	V_{DS}=V_{GS}, I_D=250 A
Drain-source on-state resistance	$R_{DS(ON)}$		6.5	8.0		V_{GS}=10 V, I_D=12 A
Drain-source on-state resistance	$R_{DS(ON)}$		8.5	10.0		V_{GS}=4.5 V, I_D=9 A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current						

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		3530		pF	V_{GS}=0 V, V_{DS}=50 V, MHz
Output capacitance	C_{oss}		560		pF	
Reverse transfer capacitance	C_{rss}		9.0		pF	
Turn-on delay time	$t_{d(on)}$		22.5		ns	V_{GS}=10 V, V_{DS}=50 V, R_G I_D=10 A
Rise time	t_r		8.6		ns	
Turn-off delay time	$t_{d(off)}$		66.6		ns	
Fall time	t_f					

Electrical Characteristics Diagrams

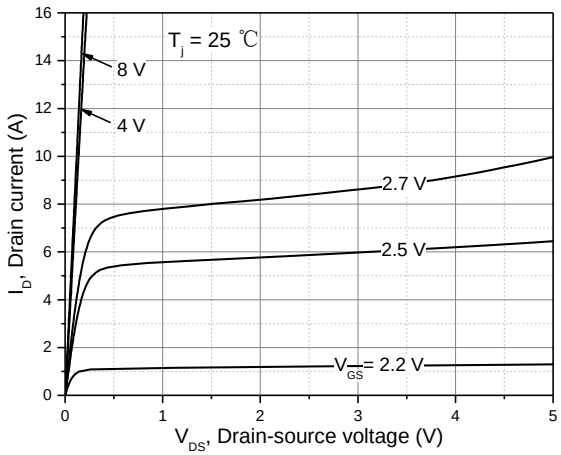


Figure 1. Typ. output characteristics

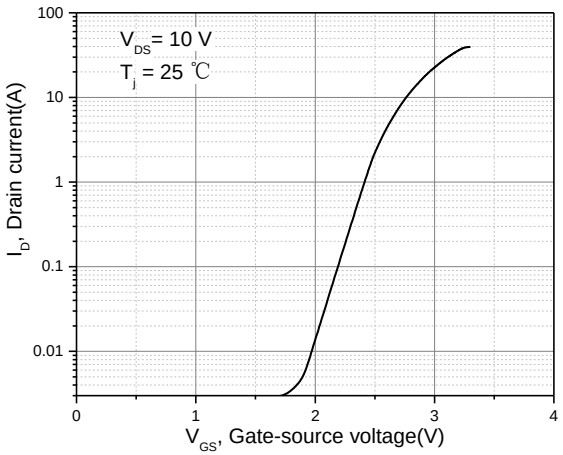


Figure 2. Typ. transfer characteristics

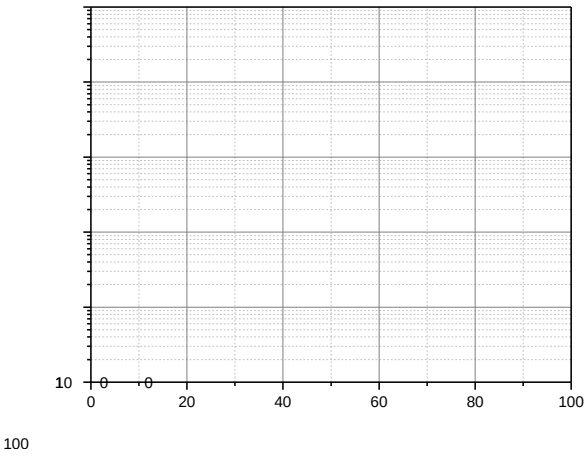


Figure 3. Typ. capacitances

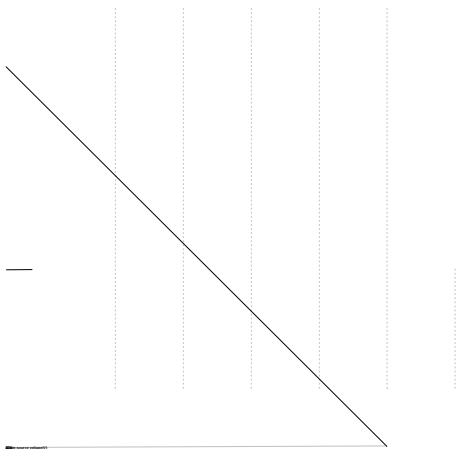


Figure 4. Typ. gate charge

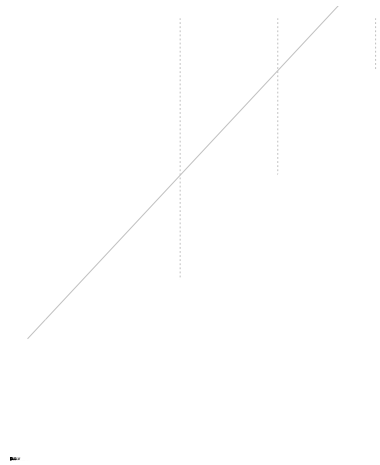


Figure 5. Drain-source breakdown voltage

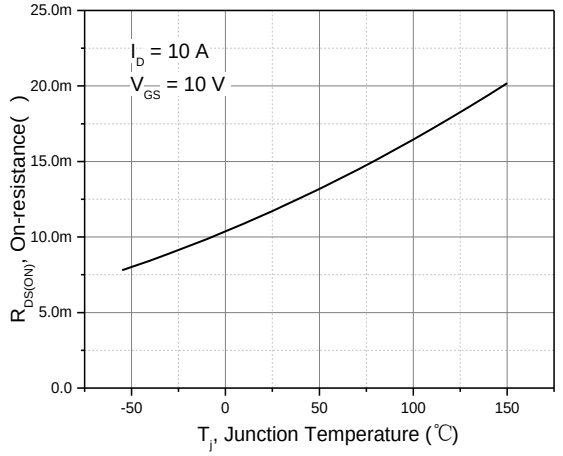


Figure 6. Drain-source on-state resistance

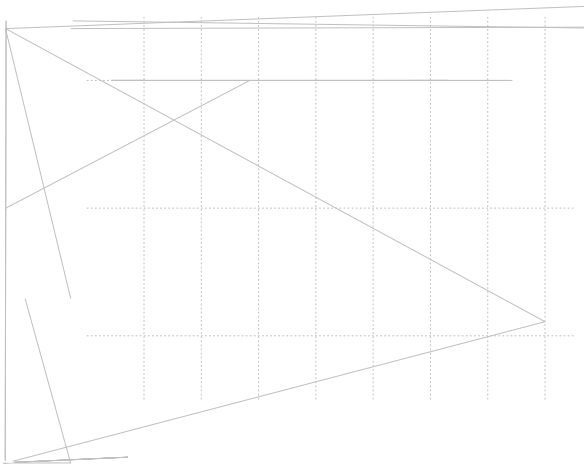


Figure 7. Drain-source on-state resistance

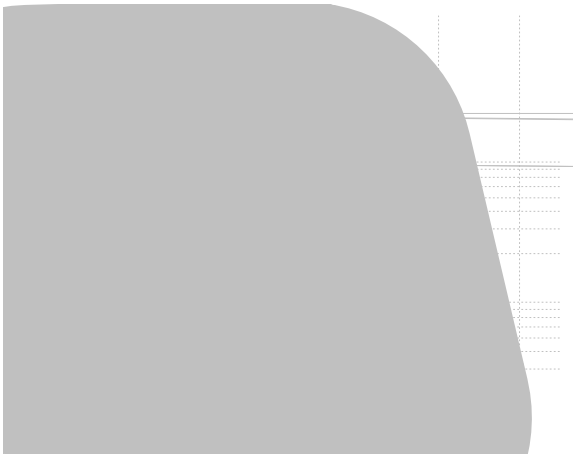


Figure 8. Forward characteristic of body diode

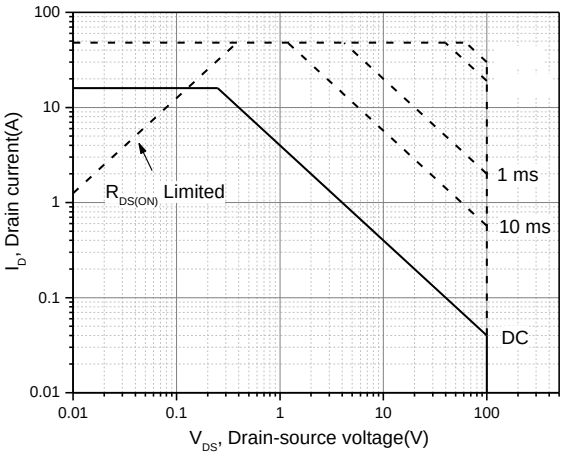


Figure 9. Safe operation area T_C=25 °C

Test circuits and waveforms

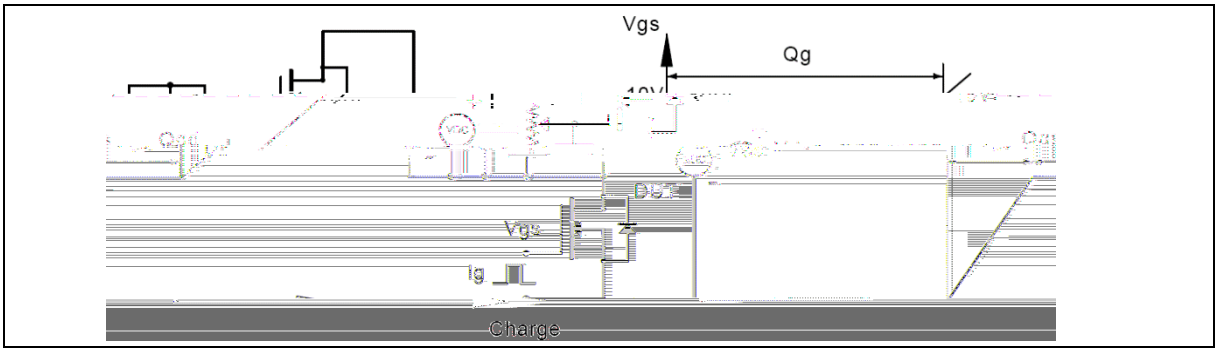


Figure 1. Gate charge test circuit & waveform

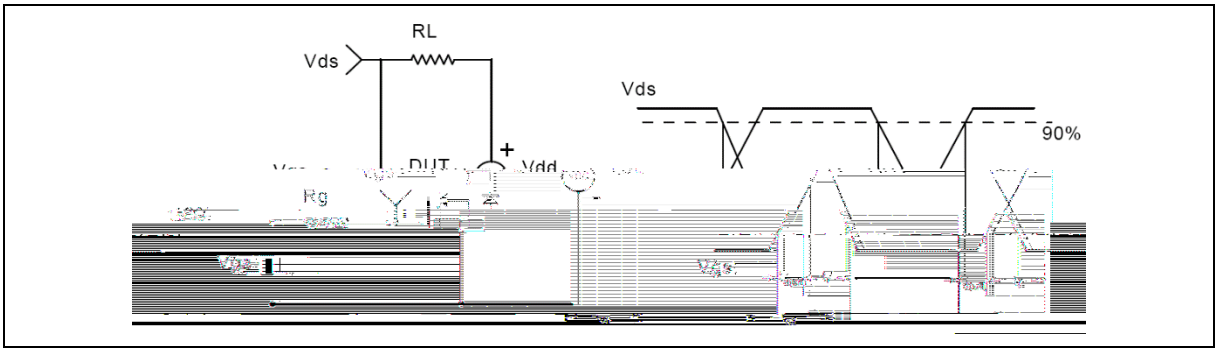


Figure 2. Switching time test circuit & waveforms

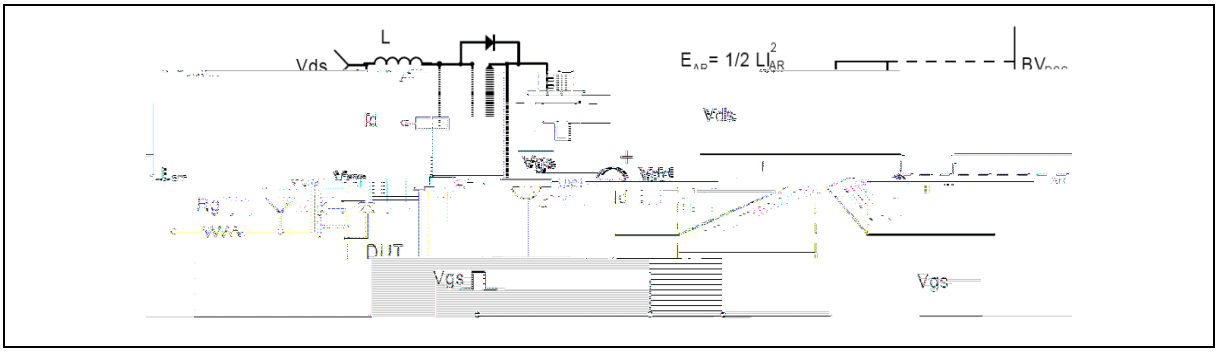


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

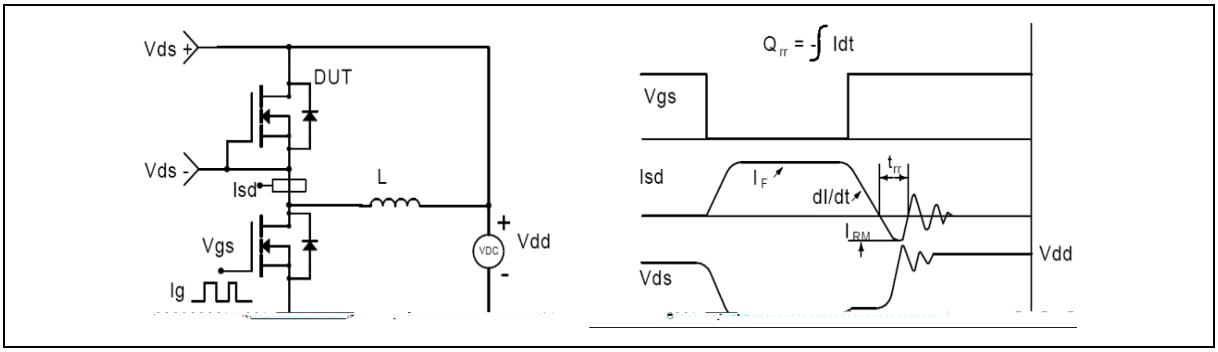
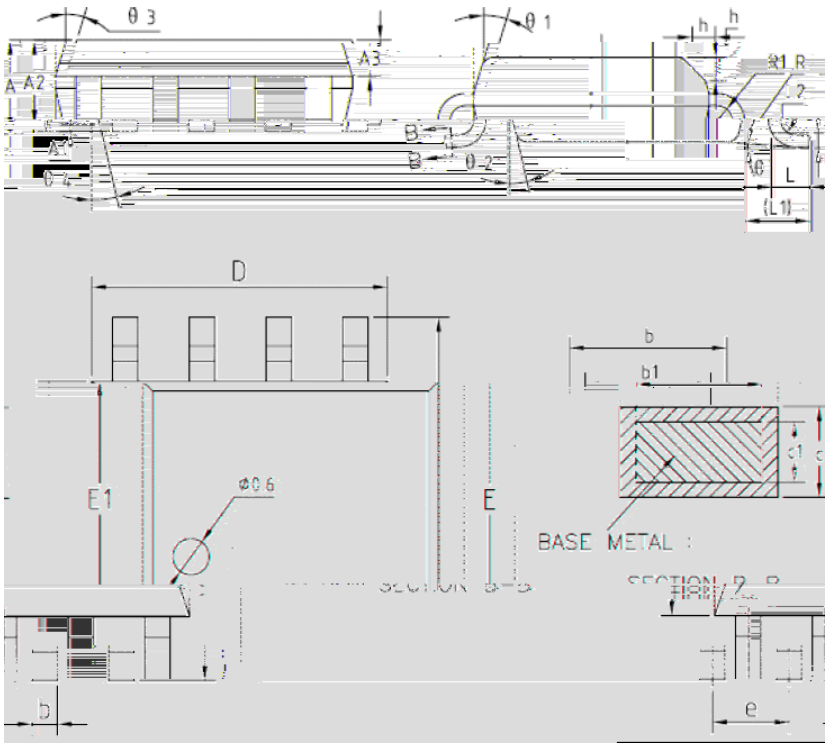


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	1.35	1.55	1.75
A1	0.10	0.15	0.25
A2	1.25	1.40	1.65
A3	0.50	0.60	0.70
b	0.38	-	0.51
L1	1.04 REF		
L2	0.25 BSC		
b1	0.37	0.42	0.47
c	0.18	-	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
R	0.07	-	-
R1	0.07	-	-
h	0.30	0.40	0.50
	0	-	

Version 1: SOP8-K package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
SOP8					